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Substitute for form 1449/A/B/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>				Application Number	09/940,792-Conf.#5268
Sheet	1	of	11	Filing Date	August 29, 2001
				First Named Inventor	Paul A. Farrar et al.
				Art Unit	2815
				Examiner Name	E.C.H. Lee
				Attorney Docket Number	M4065.0382/P382-A

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Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			
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				Application Number	09/940,792-Conf.#5268
				Filing Date	August 29, 2001
				First Named Inventor	Paul A. Farrar et al.
				Art Unit	2815
				Examiner Name	E.C.H. Lee
Sheet	8	of	11	Attorney Docket Number	M4065.0382/P382-A

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		First Named Inventor	Paul A. Farrar et al.		
		Art Unit	2815		
		Examiner Name	E.C.H. Lee		
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Examiner Signature			Date Considered	6/13/06	

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Sheet

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Application Number	09/940,792-Conf.#5268
Filing Date	August 29, 2001
First Named Inventor	Paul A. Farrar et al.
Art Unit	2815
Examiner Name	E.C.H. Lee
Attorney Docket Number	M4065.0382/P382-A

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Application Number	09/940,792
Filing Date	August 29, 2001
First Named Inventor	Paul A. Farrar
Group Art Unit	2812 > 2815
Examiner Name	D. Zarnieker Lee
Attorney Docket Number	M4065.0382/P382-A

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	U.S. Patent Document Number	Kind Code ² (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
EL	A	5,963,838		Yamamoto et al.	10/15/1999	

FOREIGN PATENT DOCUMENTS

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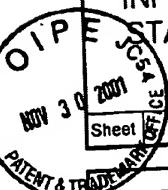
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Examiner Name	D. Zamek - Lee
Attorney Docket Number	M4065.0382/P382-A

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GL	B	F.A. Nichols, et al. - "Surface- (Interface-) and Volume-Diffusion Contributions to Morphological Changes Driven by Capillarity," Transactions of the Metallurgical Society of AIME, Volume 233, October 1965, pgs. 1840-1848*
GL	C	Tsutomu Sato, et al. - "A New Substrate Engineering for the Formation of Empty Space in Silicon (ESS) Induced by Silicon Surface Migration," 1999 IEEE, pgs. 517-520*
GL	D	U.S. Application, Serial No. 09/069,346 filed April 29, 1998, Attorney docket #303.367US1, pgs. 1-22 w/6 shts. drwgs.*

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